

Appl. No. 09/817,963

Amdt. Dated February 17, 2004

Reply to Office Action of November 17, 2003

#### CLAIM AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

#### Listing of Claims:

1-3 (Canceled).

4 (currently amended). A process for metallizing at least one insulating layer of an electronic or microelectronic component, which comprises:

applying at least one first insulating layer to a substrate such that the first insulating layer has a thickness not greater than 50 $\mu$ m;

activating ~~all of~~ the entire first insulating layer by treatment with an activator, the activator being at least one of a gas, a liquid, a solution, and a plasma;

then, after activating the entire first insulating layer, applying and patterning a second insulating layer made of a photosensitive material; and

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then, after applying and patterning the second insulating layer,  
seeding and metallizing regions of the first insulating layer  
that are exposed by the patterning step.

5 (previously presented). The process according to claim 4,  
which comprises forming the first insulating layer and the  
second insulating layer from the same material.

6 (previously presented). The process according to claim 5,  
which comprises patterning the first insulating layer before the  
second insulating layer is applied.

7 (previously presented). The process according to claim 4,  
which comprises patterning the first insulating layer before the  
second insulating layer is applied.